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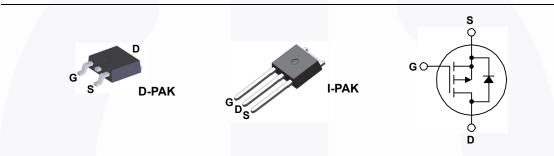
# FQD5P20 / FQU5P20 P-Channel QFET<sup>®</sup> MOSFET -200 V, -3.7 A, 1.4 Ω

## Description

This P-Channel enhancement mode power MOSFET is produced using Fairchild Semiconductor's proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state resistance, and to provide superior switching performance and high avalanche energy strength. These devices are suitable for switched mode power supplies, audio amplifier, DC motor control, and variable switching power applications

### Features

- -3.7 A, -200 V,  $\mathsf{R}_{\text{DS(on)}}$  = 1.4  $\Omega$  (Max.)@  $\mathsf{V}_{\text{GS}}$  = -10 V,  $\mathsf{I}_{\text{D}}$  =-1.85 A
- Low Gate Charge (Typ. 10 nC)
- Low Crss (Typ. 12 pF)
- 100% Avalanche Tested
- RoHS Compliant



# Absolute Maximum Ratings T<sub>C</sub> = 25°C unless otherwise noted

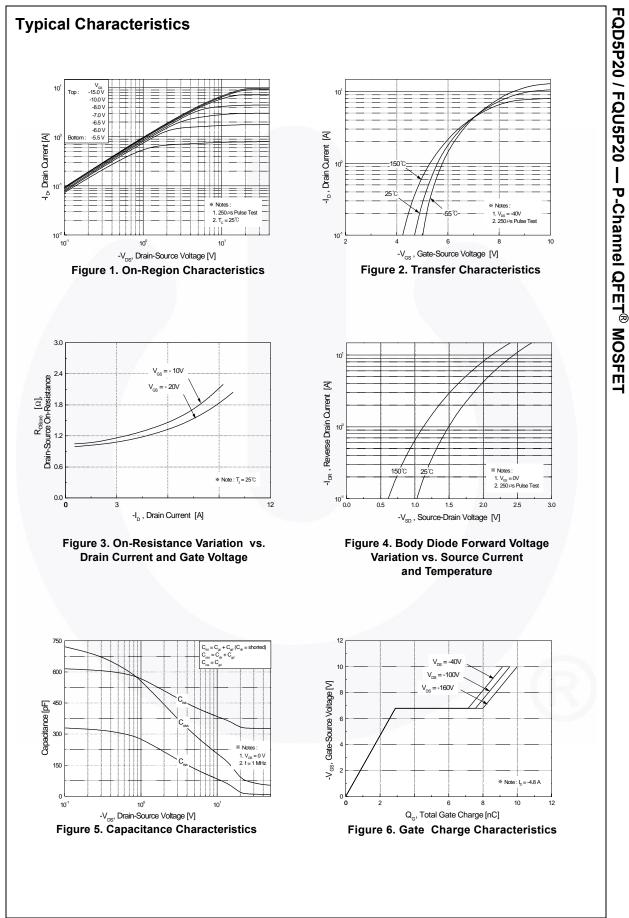
Symbol	Parameter		FQD5P20TM / FQU5P20TU	Unit
V <sub>DSS</sub>	Drain-Source Voltage		-200	V
I <sub>D</sub>	Drain Current - Continuous ( $T_C = 25^{\circ}C$ )		-3.7	А
	- Continuous (T <sub>C</sub> = 10	O°C)	-2.34	А
I <sub>DM</sub>	Drain Current - Pulsed	(Note 1)	-14.8	А
V <sub>GSS</sub>	Gate-Source Voltage		± 30	V
E <sub>AS</sub>	Single Pulsed Avalanche Energy		330	mJ
I <sub>AR</sub>	Avalanche Current	(Note 1)	-3.7	А
E <sub>AR</sub>	Repetitive Avalanche Energy	(Note 1)	4.5	mJ
dv/dt	Peak Diode Recovery dv/dt	(Note 3)	-5.5	V/ns
P <sub>D</sub> Power Dissipation ( $T_A = 25^{\circ}C$ ) *		2.5	W	
	Power Dissipation (T <sub>C</sub> = 25°C)		45	W
- Derate above 25°C			0.36	W/°C
T <sub>J</sub> , T <sub>STG</sub>	STG Operating and Storage Temperature Range		-55 to +150	°C
Τ <sub>L</sub>	Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds		300	°C

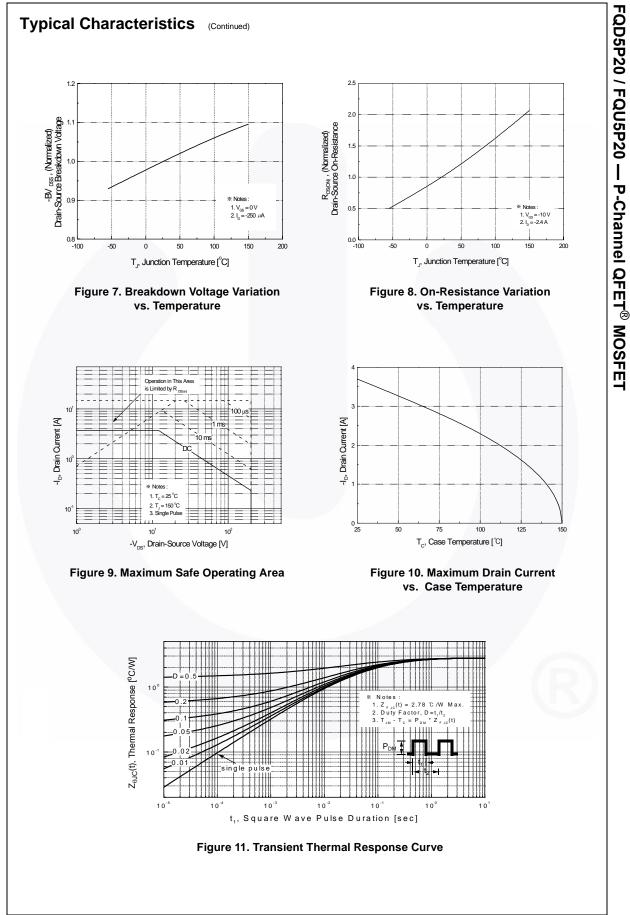
# **Thermal Characteristics**

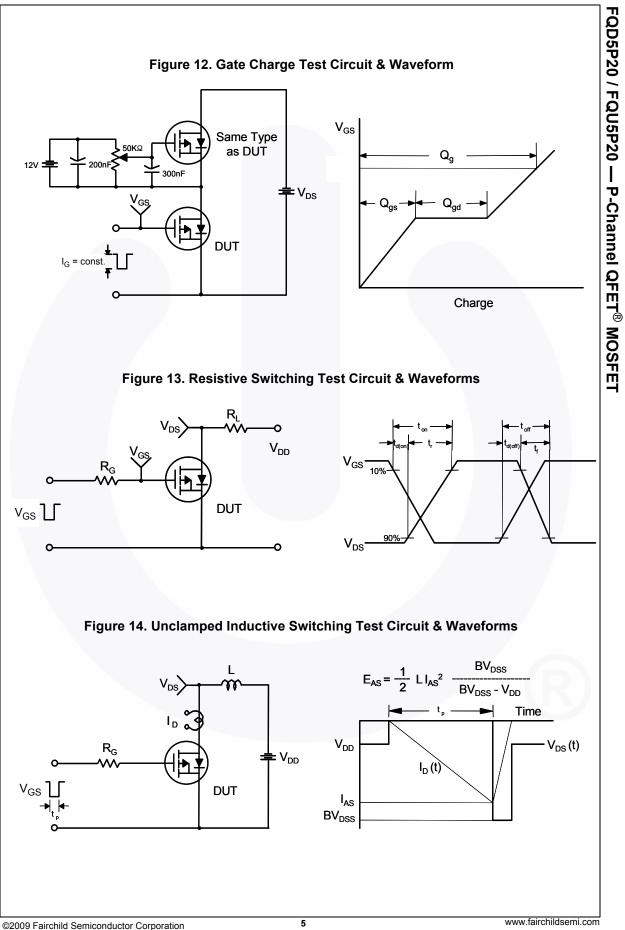
Symbol	Parameter	FQD5P20TM FQU5P20TU	Unit	
$R_{ ext{ heta}JC}$	Thermal Resistance, Junction to Case, Max.	2.78		
$R_{\thetaJA}$	Thermal Resistance, Junction to Ambient (minimum pad of 2 oz copper), Max.	110	°C/W	
	Thermal Resistance, Junction to Ambient (* 1 in <sup>2</sup> pad of 2 oz copper), Max.	50		

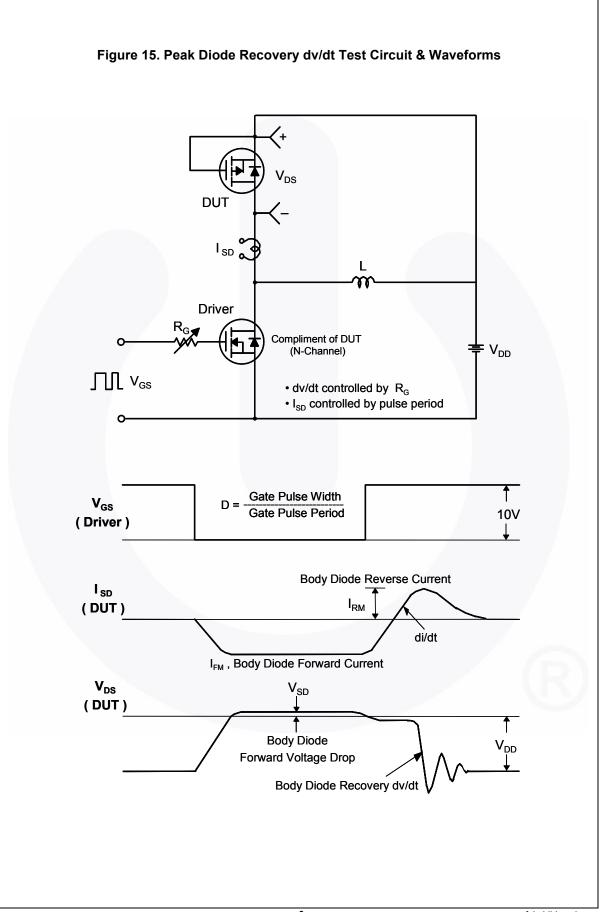
FQD5P20 / FQU5P20 — P-Channel QFET<sup>®</sup> MOSFET

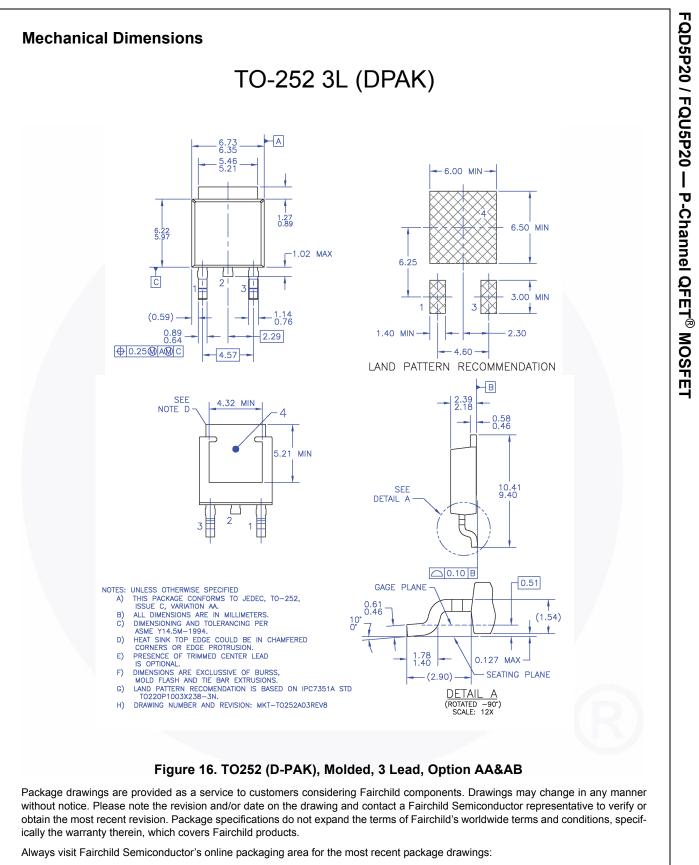
Device Marking		Device	Package	Reel Size	Tape W	/idth	Qua	intity	
-		DPAK	DPAK 330 mm		16 mm		2500		
FQU5	P20	FQU5P20TU	IPAK	PAK -		-		70	
erica	l Char	acteristics T <sub>c = 25</sub> %	C unless otherwise	noted					
ymbol		Parameter	Т	est Conditions	Min	Тур	Max	Unit	
	aracteri					-76			
V <sub>DSS</sub>	Drain-S	ource Breakdown Voltage	V <sub>GS</sub> = 0 \	/, I <sub>D</sub> = -250 μA	-200			V	
BV <sub>DSS</sub> ΔT <sub>J</sub>	Breakdo Coefficio	own Voltage Temperature ent	I <sub>D</sub> = -250	μA, Referenced to 25°C		-0.17		V/°C	
DSS				00 V, V <sub>GS</sub> = 0 V			-1	μA	
	∠ero Ga	te Voltage Drain Current	-	50 V, T <sub>C</sub> = 125°C			-10	μΑ	
GSSF	Gate-Bo	ody Leakage Current, Forwa	_	$0 \text{ V}, \text{ V}_{\text{DS}} = 0 \text{ V}$			-100	nA	
GSSR	Gate-Bo	dy Leakage Current, Revers	e V <sub>GS</sub> = 30	V, V <sub>DS</sub> = 0 V			100	nA	
On Cha	racteri	stics				L		L	
GS(th)	Gate Th	reshold Voltage	$V_{DS} = V_{G}$	<sub>iS</sub> , I <sub>D</sub> = -250 μA	-3.0		-5.0	V	
CDS(on)	Static D On-Res	rain-Source istance	V <sub>GS</sub> = -10	0•V, I <sub>D</sub> = −1.85 A		1.1	1.4	Ω	
FS	Forward	I Transconductance	$V_{DS} = -40$	0 V, I <sub>D</sub> = -1.85 A		2.2		S	
Dynami C <sub>iss</sub>	1	acteristics apacitance				330	430	pF	
	-	Capacitance		5 V, V <sub>GS</sub> = 0 V,		75	98	pF	
rss		e Transfer Capacitance	f = 1.0 MI			12	15	pF	
	1	racteristics					10	P.	
d(on)		Delay Time				9	28	ns	
r		Rise Time		00 V, I <sub>D</sub> = -4.8 A,		70	150	ns	
		f Delay Time	R <sub>G</sub> = 25 9	.2		12	35	ns	
				(Note 4)		25	60	ns	
d(off)							13	nC	
d(off)		f Fall Time ate Charge	V16	SO V I4 8 A		10			
d(off) f Qg	Total Ga	ate Charge		60 V, I <sub>D</sub> = -4.8 A,		10 2.8		nC	
d(off) f Q <sub>g</sub> Q <sub>gs</sub>	Total Ga Gate-So	ate Charge burce Charge	V <sub>DS</sub> = -16 V <sub>GS</sub> = -10	-		2.8		nC nC	
d(off) f 2 <sub>g</sub> 2 <sub>gs</sub> 2 <sub>gd</sub>	Total Ga Gate-So Gate-Dr	ate Charge ource Charge rain Charge <b>Diode Characteristics</b>	V <sub>GS</sub> = -10	∩ V (Note 4) num Ratings				nC nC	
l(off) Qg Qgs Qgd Drain-S	Total Ga Gate-So Gate-Dr	ate Charge ource Charge ain Charge	V <sub>GS</sub> = -10	∩ V (Note 4) num Ratings		2.8		_	
d(off) 2 <sub>g</sub> 2 <sub>gs</sub> 2 <sub>gd</sub> <b>Drain-S</b> S	Total Ga Gate-So Gate-Dr Gource I Maximu	ate Charge ource Charge rain Charge <b>Diode Characteristics</b>	V <sub>GS</sub> = -10 and Maxin Diode Forward	Note 4)		2.8 5.2		nC	
d(off) 2 <sub>g</sub> 2 <sub>gs</sub> 2 <sub>gd</sub> <b>Drain-S</b> S	Total Ga Gate-Sc Gate-Dr <b>Cource I</b> Maximu Maximu	ate Charge purce Charge ain Charge <b>Diode Characteristics</b> m Continuous Drain-Source	V <sub>GS</sub> = -10 and Maxin Diode Forward le Forward Cu	Note 4)		2.8 5.2		nC A	
d(off) f 2 <sub>g</sub> 2 <sub>gs</sub> 2 <sub>gd</sub>	Total Ga Gate-So Gate-Dr Source I Maximu Maximu Drain-S	ate Charge purce Charge ain Charge <b>Diode Characteristics</b> m Continuous Drain-Source m Pulsed Drain-Source Dioc	$V_{GS} = -10$ and Maxim Diode Forward le Forward Cu $e$ $V_{GS} = 0.1$	Note 4) num Ratings d Current rrent		2.8 5.2	  -3.7 -14.8	nC A A	





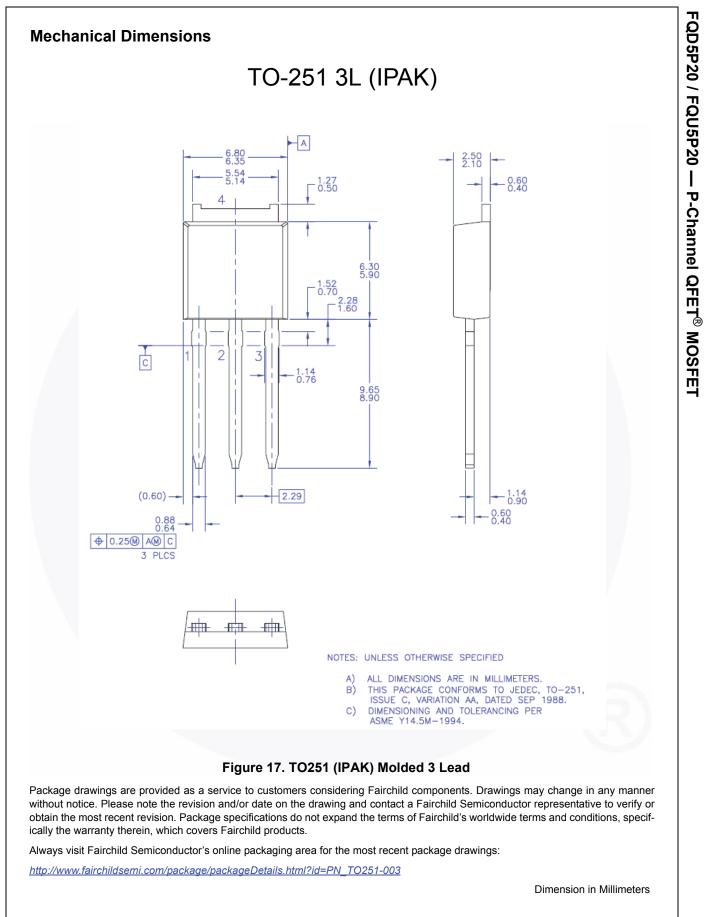






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**Dimension in Millimeters** 





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